

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Serial No.: Randall, et al.

Herewith

Filed:

Herewith

Group Art Unit:

Examiner:

Title:

SNAP-IN PANEL DESIGN FOR A REFRIGERATION COOLER

RESUBMITTAL OF INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

This paper is responsive to the Office Action mailed on June 22, 2005.

A duplicate copy of the Information Disclosure Statement filed with the Patent Office on July 31, 2003 as well as duplicate copies of the Non Patent Literature Documents are attached.

Respectfully submitted,

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Dated: August 9, 2005



CERTIFICATE OF MAILING

I hereby certify that the enclosed **Resubmittal of Information Disclosure Statement** is being deposited with the United States Postal Service as First Class Mail, postage prepaid, in an envelope addressed to Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on August 9, 2005.

Theresa M. Palmateer

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Nishikawa et al. (US 4,711,809).

Nishikawa describes a method for depositing a fluorine-containing organic film using hexafluorobutadiene (col. 4, line 4-15, 41) (claimed C4F6, of which global warming potential is less than 100). Since the same gas is used, it would produce a layer with a relative dielectric constant of 4 or less on the magnetic recording medium (claimed semiconductor substrate).

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claim 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over Xi et al. (US 6,211,065) and Nishikawa et al. (US 4,711,809).

Xi describes a deposition method of amorphous fluorocarbon (claimed fluorinecontaining organic film) having a low dielectric constant as slow as 2.3 using a fluorine source Application/Control Number: 10/600,606

Art Unit: 1765

gas, such as CF4, C2F6, C3F8, C6F6, as the main component (col. 2, line 4-6; col. 12, line 34-44). Unlike claimed invention, he doesn't describe using fluorine gas such as C4F6. Nishikawa shows that at time of the invention, gases such as C4F6, of which global warming potential is less than 100, has been known and used by one skilled in the art to deposit fluorine-containing organic layer (col. 4, line 4-15, 41). It would have been obvious to one skilled in the art to use other fluorine gas such as C4F6 in light of Nishikawa and Xi's teaching of using gas having atomic ratios of F:C less than 2 to deposit the fluorine-containing organic layer with an anticipation of an expected result.

4. Claims 2-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al. (US 6,057,239), Xi et al. (US 6,211,065), Nishikawa et al. (US 4,711,809), and Imai et al. (US 6,057,247).

Wang describes a method for forming a semiconductor device comprising: dry-etching an oxide film (claimed insulating film); depositing a low dielectric organic film (col. 3, line 40-60). Unlike claimed invention, Wang doesn't describe the etching gas containing C4F6 as a main component. However, using gas such as C5F8, C4F6, or C3F6 as the main component for etching oxide film has been known to one skill in the art as taught by Imai (col. 15, line 6-7; col. 20, line 29-32). Therefore at the time of the invention, one skill in the art would find it obvious to etch the insulating film in light of Imai because Imai further describes techniques to etch the insulating film used by Wang in order to etch the insulating film.

Unlike claimed invention, Wang doesn't describe depositing a fluorine-containing organic film. However, he describes using low dielectric film and amorphous fluorocarbon is a low dielectric organic film as taught by Xi. Xi describes a deposition method of amorphous